



650V 16A 0.48Ω N-ch Power MOSFET

Description

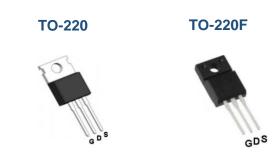
DT2 MOS is DIN-TEK 2nd generation VDMOS family that is dramatic reduction in on-resistance and ultra-low gate charge for applications requiring high power density and high efficiency. And it is very robust and RoHS compliant.

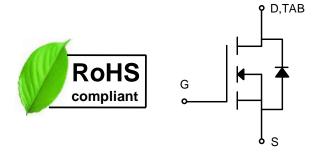
Features

- Typ.R_{DS(on)}=0.48 Ω @V_{GS}=10V
- 100% avalanche tested
- RoHS Compliant

Applications

- SMPS
- Charger
- DC-DC





Absolute Maximum Ratings (Tc=25℃)

Parameter	Symbol	DTP16N65	DTP16N65F	Unit	
Drain-source voltage	V _{DSS}	6	650	V	
Gate-source voltage	V _G S	<u>+</u>	-30	V	
Continuous drain current	ID		16	А	
Pulsed drain current ¹	I _{DM}	64			
Avalanche energy, single pulse ²	Eas	980			
Power dissipation	P _D	156	62.5	W	
Derate above 25°C		1.3 0.5		W/°C	
Operating junction temperature	Tj	-55~150		°C	
Storage temperature	T _{stg}	-55~150			
Continuous diode forward current	Is	16			
Diode pulse current ¹	I _{Spulse}	64			

Thermal Characteristic

Thermal resistance, junction-to-case	$R_{ heta JC}$	0.8	2	°C/W
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	30	62.5	°C/W



DTP16N65/DTP16N65F

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Flectrical	Characteristics	of MOSEET
Electrical	Character Istics	UI WUSEEI

Electrical Characteristics of i	VIOSFEI			Min.	Тур.	Max.	
Drain-source break down voltage	BV _{DSS}	I _D =250µA, V _{GS} =0V	Tc=25°C	650	-	-	V
Gate threshold voltage	V _{GS(th)}	I _D =250µA, V _{DS} =V _{GS}	TJ=25°C	2.0	-	4.0	V
Drain-source leakage current	I _{DSS}	V _{DS} =650V, V _{GS} =0V	TJ=25°C	-	-	1	μA
		V _{DS} =520V, V _{GS} =0V	TJ=125°C	-	-	100	μA
Gate-source leakage current,forward	IGSSF	V _{DS} =0V, V _{GS} =30V	TJ=25°C	-	-	100	nA
Gate-source leakage current,reverse	Igssr	V _{DS} =0V, V _{GS} =-30V	TJ=25°C	-	-	-100	nA
Drain-source on-state resistance ³	R _{DS(ON)}	V _{GS} =10V, I _D =8A	TJ=25°C	-	0.48	0.58	Ω

Dynamic Characteristics of MOSFET (Tc=25℃)

Dynamic Characteristics of WOSFLT (10=25 C)			Min.	Тур.	Max.	
Input capacitance	Ciss		-	2740	-	pF
Output capacitance	Coss	f=1MHz, V _{DS} =25V, V _{GS} =0V	-	215	-	pF
Reverse transfer capacitance	C _{rss}		-	15	-	pF
Gate to source charge	Qgs	V _{DD} =300V	-	16	-	nC
Gate to drain charge	Q_{gd}	I _D =16A	-	16	-	nC
Total gate charge	Qg	V _{GS} = 0 to10V	-	61	-	nC

Switching Characteristics of MOSFET $(T_C=25^{\circ}C)$

Switching Characteristics of MOSPET (1c=25 C)			Min.	Тур.	Max.	
Turn-on delay time	t _{d on}		-	35	-	ns
Rise time	tr	V _{DS} =320V, I _D =16A,	-	50	-	ns
Turn-off delay time	t _{d off}	$R_G=25\Omega$, $V_{GS}=0$ to $10V$	-	160	-	ns
Fall time	t _f		-	65	-	ns

Characteristics of Body Diode (T_C=25℃)

onaractoristics of Body Blods (10-25 C)			Min.	Тур.	Max.	
Forward voltage	V _{SD}	I _{SD} =16A, V _{GS} =0V	1	-	1.4	V
Reverse recovery time	t _{rr}	$ \begin{array}{c c} \hline t_{rr} & \\ \hline I_{rr} & \\ \hline Q_{rr} & \\ \hline \end{array} \\ V_{DS} = 320 V, \ I_{S} = 16 A, \ V_{GS} = 10 V \\ \hline - \\ \hline - \\ \hline \end{array} $	-	574	-	ns
Reverse recovery current	Irr		-	20	-	Α
Recovery charge	Qrr		-	5.7	-	μC

Notes:

- 1. Repetitive rating, pulse width limited by junction temperature $T_{\text{J(MAX)}}$ =150°C.
- 2. The EAS data shows Max. rating . The test condition is V_{DD} =50V, V_{GS} =10V, L=10mH, IAS =14A,Tc=25°C.
- 3. The data tested by pulsed , pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%.$

TYPICAL CHARACTERISTICS

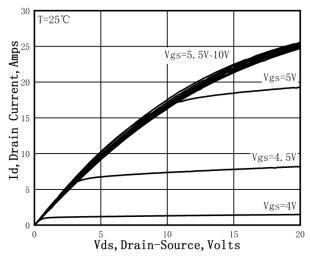


Figure 1.On-Region Characteristics

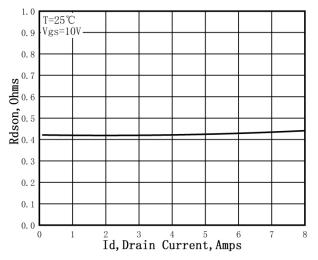


Figure 3. Static Drain-Source On Resistance

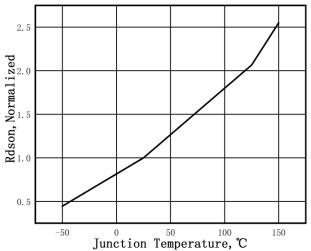


Figure 5. Normalized R_{DS(on)} vs.Temperature

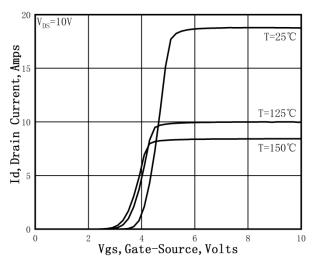


Figure 2. Transfer Characteristics

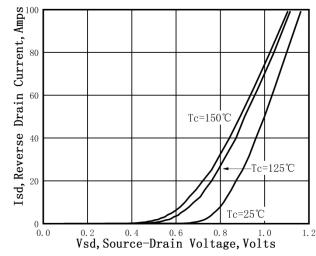


Figure 4. Typical Body Diode Transfer

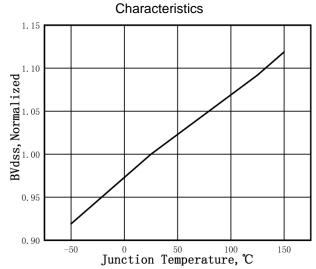
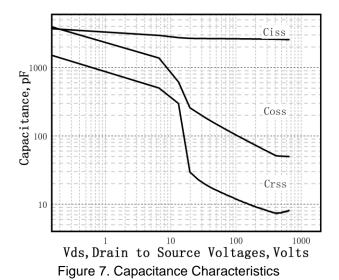


Figure 6. Normalized BV_{DSS} vs.Temperature



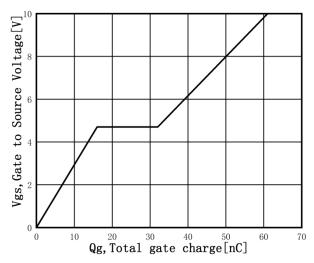
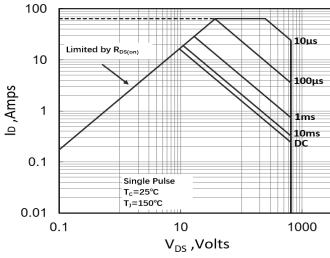


Figure 8. Gate Charge Characteristics



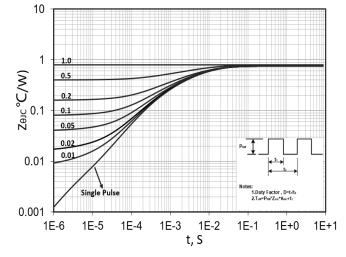
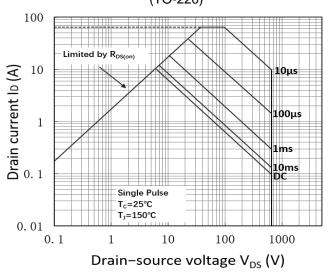


Figure 9. Maximum Safe Operating Area (TO-220)

Figure 10. Transient Thermal Response Curve (TO-220)



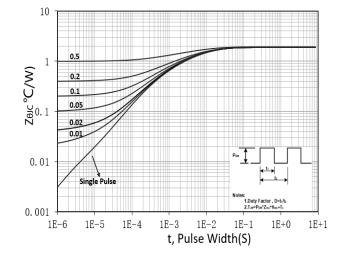
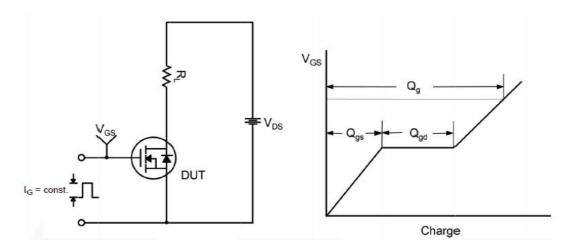


Figure 11. Maximum Safe Operating Area (TO-220F)

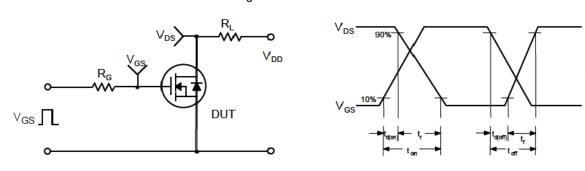
Figure 12. Transient Thermal Response Curve (TO-220F)

Test Circuit

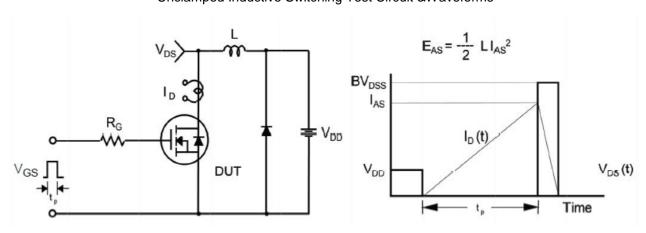
Gate Charge Test Circuit &Waveform



Switching Test Circuit &Waveforms

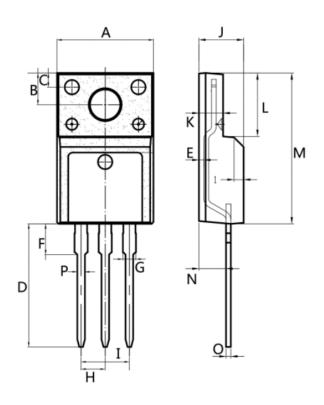


Unclamped Inductive Switching Test Circuit &Waveforms





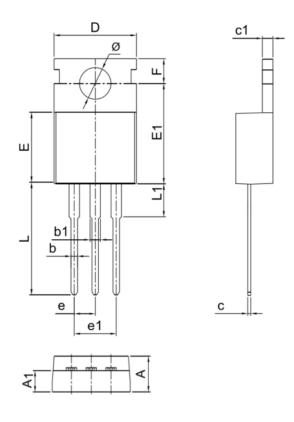
Mechanical Dimensions for TO-220F



COMMON DIMENSIONS

SYMBOL	M	М
STIVIBUL	MIN	MAX
Α	9.95	10.36
В	2.95	3.55
С	1.25	1.6
D	12.64	13.5
E	0.40	0.60
F	2.80	3.80
G	1.14	1.58
Н	2.44	2.64
I	4.88	5.26
J	4.50	4.90
K	2.34	2.80
L	6.48	6.90
M	15.40	16.07
N	2.66	3.50
0	0.40	0.64
Р	0.70	0.94

Mechanical Dimensions for TO-220



COMMON DIMENSIONS

SYMBOL	M	М
STIVIBUL	MIN	MAX
Α	4.30	4.70
A1	2.30	2.82
b	0.70	0.94
b1	1.17	1.41
С	0.30	0.64
c1	1.17	1.44
D	9.70	10.20
Е	8.50	9.30
E1	12.00	12.50
е	2.44	2.64
e1	4.88	5.26
F	2.60	2.94
L	13.00	14.00
L1	3.385	4.20
Ø	3.74	3.95





Ordering Information

Part	Package	Packing method
DTP16N65F	TO-220F	Tube
DTP16N65	TO-220	Tube





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